

International Rectifier

HFA15TB60 HFA15TB60-1

Bulletin PD -2.334 rev. B 01/02

HEXFRED™

Ultrafast, Soft Recovery Diode

Features

- Ultrafast Recovery
- Ultrasoft Recovery
- Very Low I_{RRM}
- Very Low Q_{rr}
- Specified at Operating Conditions

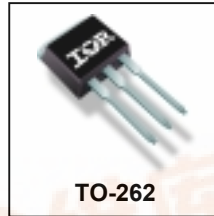
Benefits

- Reduced RFI and EMI
- Reduced Power Loss in Diode and Switching Transistor
- Higher Frequency Operation
- Reduced Snubbing
- Reduced Parts Count

Description

International Rectifier's HFA15TB60 is a state of the art ultra fast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 volts and 8 amps per Leg continuous current, the HFA15TB60 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultra fast recovery time, the HEXFRED product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA15TB60 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

$V_R = 600V$
$V_F = 1.7V$
$Q_{rr}^* = 84nC$
$di_{(rec)}/dt^* = 188A/\mu s$
* 125°C



Absolute Maximum Ratings

	Parameter	Max	Units
V_R	Cathode-to-Anode Voltage	600	V
$I_F @ T_C = 100^\circ C$	Continuous Forward Current	15	
I_{FSM}	Single Pulse Forward Current	150	A
I_{FRM}	Maximum Repetitive Forward Current	60	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	74	
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	29	W
T_J	Operating Junction and		
T_{STG}	Storage Temperature Range	- 55 to +150	C



Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
V_{BR}	Cathode Anode Breakdown Voltage	600			V	$I_R = 100\mu\text{A}$
V_{FM}	Max Forward Voltage		1.3	1.7	V	$I_F = 15\text{A}$ $I_F = 30\text{A}$ See Fig. 1
			1.5	2.0		
			1.2	1.6		
I_{RM}	Max Reverse Leakage Current		1.0	10	μA	$V_R = V_R$ Rated See Fig. 2 $T_J = 125^\circ\text{C}$, $V_R = 0.8 \times V_R$ Rated
			400	1000		
C_T	Junction Capacitance		25	50	pF	$V_R = 200\text{V}$ See Fig. 3
L_S	Series Inductance		8.0		nH	Measured lead to lead 5mm from package body

Dynamic Recovery Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
t_{rr}	Reverse Recovery Time		19		ns	$I_F = 1.0\text{A}$, $di/dt = 200\text{A}/\mu\text{s}$, $V_R = 30\text{V}$ $T_J = 25^\circ\text{C}$
t_{rr1}	See Fig. 5, 6 & 16		42	60		
t_{rr2}			74	120		
I_{RRM1}	Peak Recovery Current		4.0	6.0	A	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
I_{RRM2}	See Fig. 7 & 8		6.5	10		
Q_{rr1}	Reverse Recovery Charge		84	180	nC	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
Q_{rr2}	See Fig. 9 & 10		241	600		
$di_{(rec)M}/dt1$	Peak Rate of Fall of Recovery Current		188		A/ μs	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$
$di_{(rec)M}/dt2$	During t_b See Fig. 11 & 12		160			

Thermal - Mechanical Characteristics

	Parameter	Min	Typ	Max	Units
T_{lead} ①	Lead Temperature			300	$^\circ\text{C}$
R_{thJC}	Thermal Resistance, Junction to Case			1.7	K/W
R_{thJA} ②	Thermal Resistance, Junction to Ambient			80	
R_{thCS} ③	Thermal Resistance, Case to Heat Sink		0.5		
Wt	Weight		2.0		g
			0.07		(oz)
T	Mounting Torque		6.0	12	Kg-cm
			5.0	10	lbf-in

① 0.063 in. from Case (1.6mm) for 10 sec

② Typical Socket Mount

③ Mounting Surface, Flat, Smooth and Greased

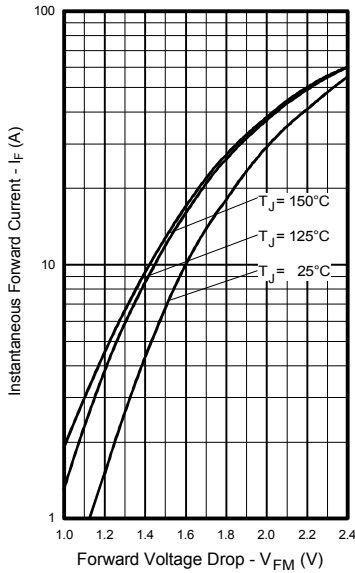


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

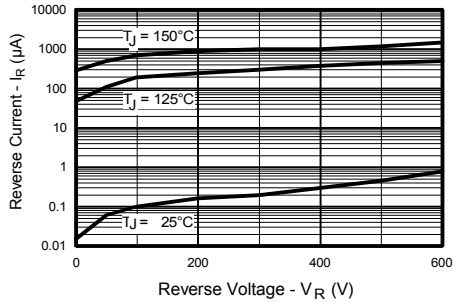


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

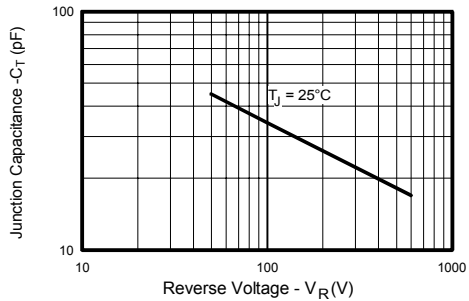


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

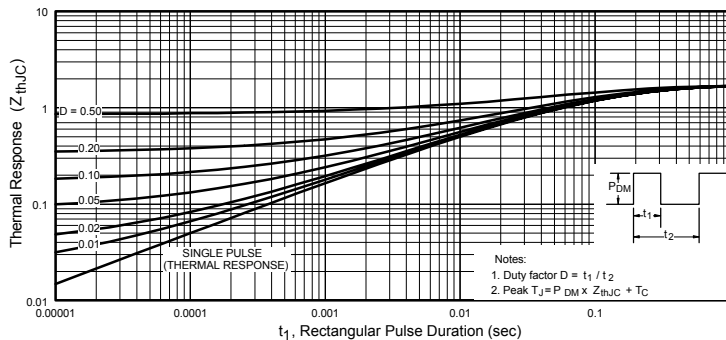


Fig. 4 - Maximum Thermal Impedance Z_{thjC} Characteristics

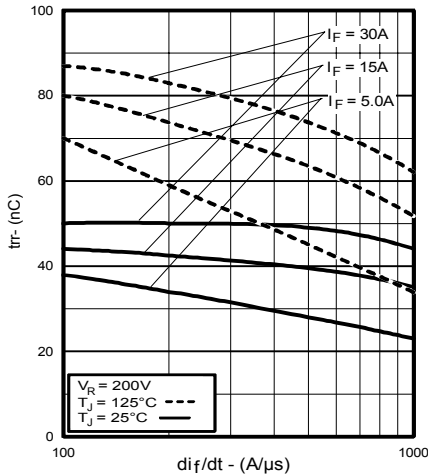


Fig. 5 - Typical Reverse Recovery vs. di_f/dt

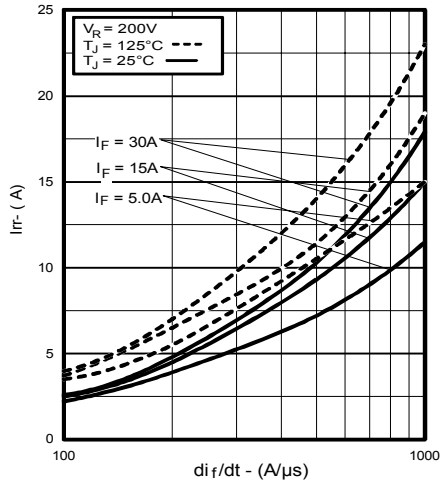


Fig. 6 - Typical Recovery Current vs. di_f/dt

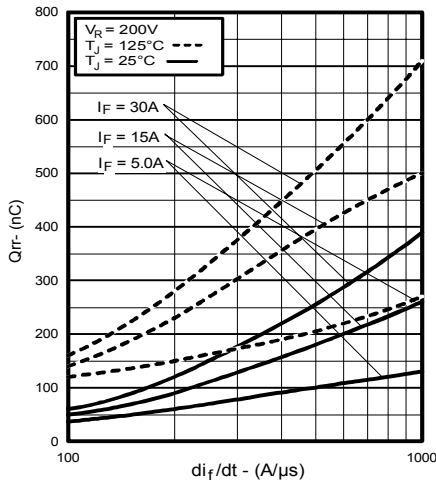


Fig. 7 - Typical Stored Charge vs. di_f/dt

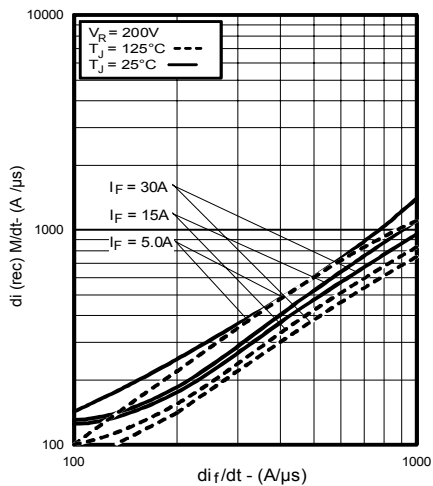


Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

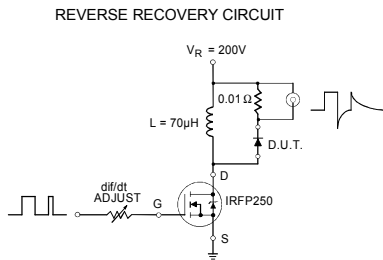
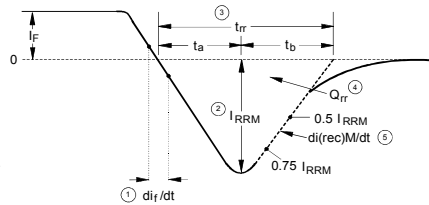


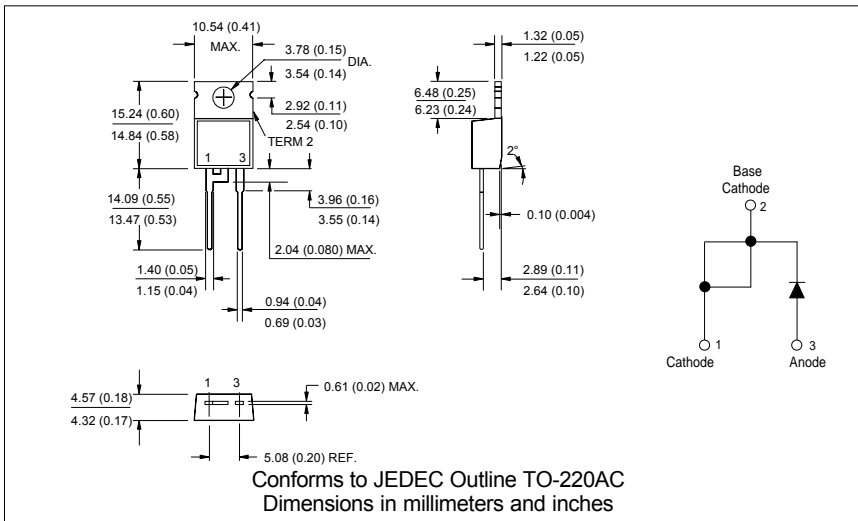
Fig. 9 - Reverse Recovery Parameter Test Circuit



- di_r/dt - Rate of change of current through zero crossing
 - I_{RRM} - Peak reverse recovery current
 - t_{rr} - Reverse recovery time measured from zero crossing point of negative going I_r to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current
 - Q_{rr} - Area under curve defined by t_r and I_{RRM}
 - $di_{(rec)}/dt$ - Peak rate of change of current during t_b portion of t_r
- $$Q_{rr} = \frac{t_r \times I_{RRM}}{2}$$

Fig. 10 - Reverse Recovery Waveform and Definitions

Outline Table

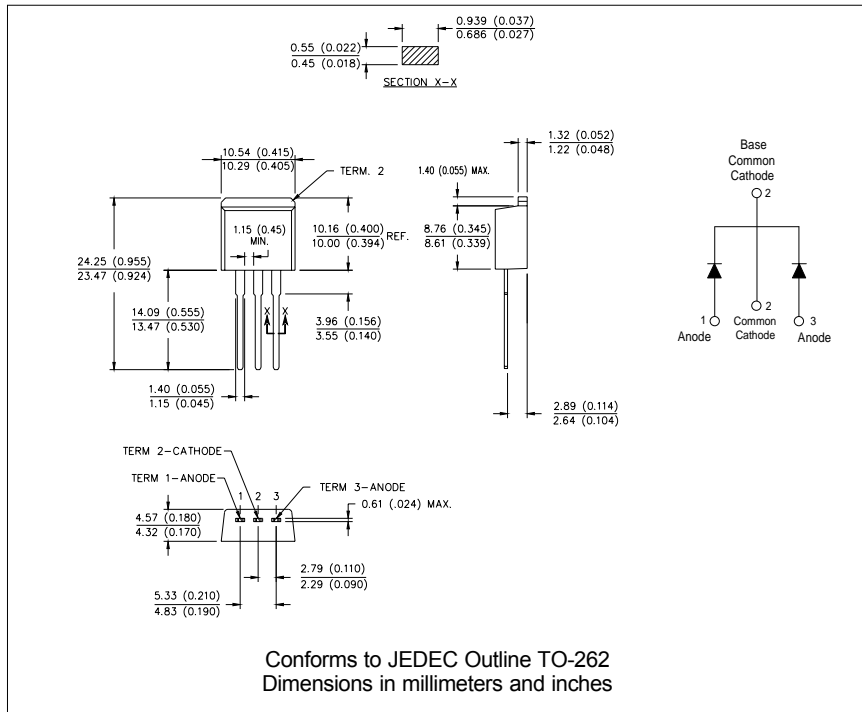


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Outline Table



Data and specifications subject to change without notice.
 This product has been designed and qualified for Industrial Level.
 Qualification Standards can be found on IR's Web site.

International
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